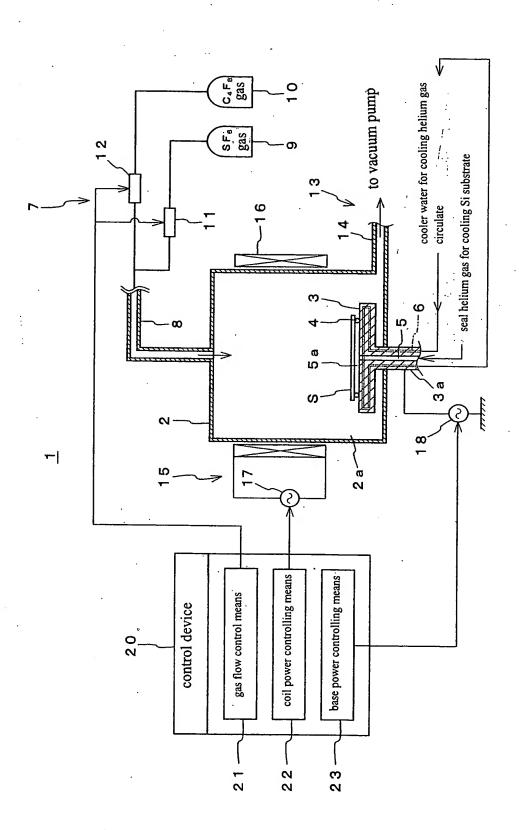
Docket No.: 20110/0200839-US0

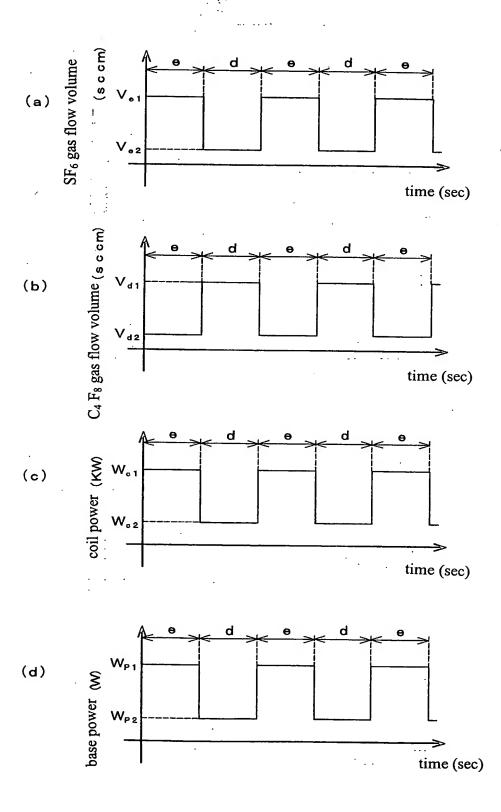
App No.: Not Yet Assigned Docket No.: 20110/0200 Inventor: Kazuo Kasai et al. Title: SĮLICON SUBSTRATE ETCHING METHOD AND ETCHING APPARATUS

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App No.: Not Yet Assigned Docket No.: 20110/0200839-US0 Inventor: Kazuo Kasai et al.
Title: SILICON,SUBSTRATE ETCHING METHOD AND
ETCHING APPARATUS
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Fig. 2

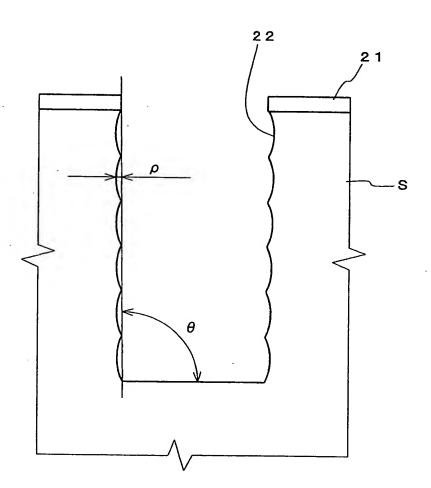


App No.: Not Yet Assigned
Inventor: Kazuo Kasai et al.
Title; SILICON ŞUBSTRATE ETCHING METHOD AND
ETCHING APPARATUS

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Fig. 3



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Fig. 4

	embodiment	comparative example
etching rate (μm/min)	3. 7	3. 4
mask selection ratio	140	104
unevenness	160	250
hole side wall angle	90. 2	90. 5

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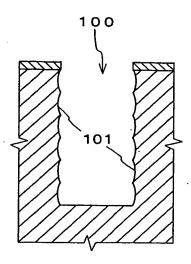


Fig. 5

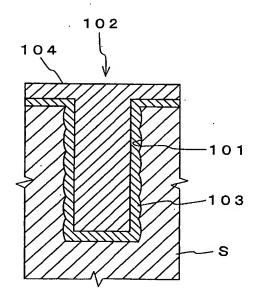


Fig. 6